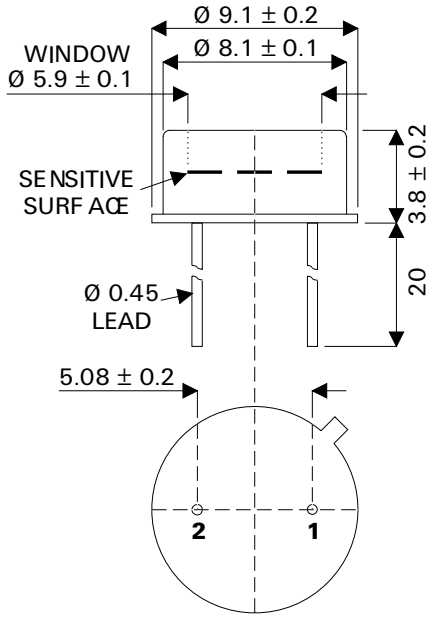
SMP550G-EM

MECHANICAL DATA
Dimensions in mm.

P.I.N. PHOTODIODE



TO-39 Package

Pin 1 – Anode

Pin 2 – Cathode & Case

FEATURES

- **VISIBLE AND UV BLIND**
- **EXCELLENT LINEARITY**
- **LOW NOISE**
- **WIDE SPECTRAL RESPONSE**
- **LOW LEAKAGE CURRENT**
- **LOW CAPACITANCE**
- **RG850 INTEGRAL OPTICAL FILTER**
- **TO39 HERMETIC METAL CAN PACKAGE**
- **EMI SCREENING MESH AVAILABLE**

DESCRIPTION

The SMP550G-EM is a Silicon P.I.N. photodiode incorporated in a hermetic metal can package. The electrical terminations are via two leads of diameter 0.018" on a pitch of 0.2". The can structure incorporates an optical filter that only transmits infra-red light. The cathode of the photodiode is electrically connected to the package.

The larger photodiode active area provides greater sensitivity than the SMP400 range of devices, with a corresponding reduction in speed. The photodiode structure has been optimised for high sensitivity, light measurement applications. The metal can and optional screening mesh ensure a rugged device with a high degree of immunity to radiated electrical interference.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

Operating temperature range	-40°C to +70°C
Storage temperature range	-45°C to +80°C
Temperature coefficient of responsively	0.35% per °C
Temperature coefficient of dark current	x2 per 8°C rise
Reverse breakdown voltage	60V

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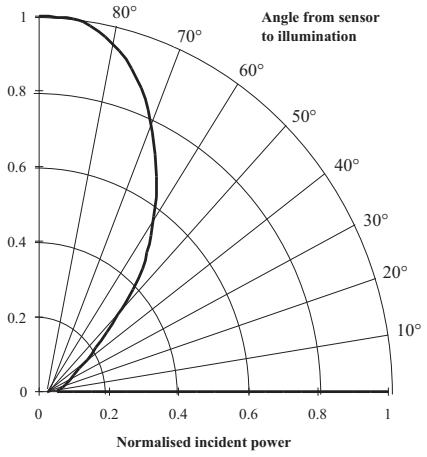
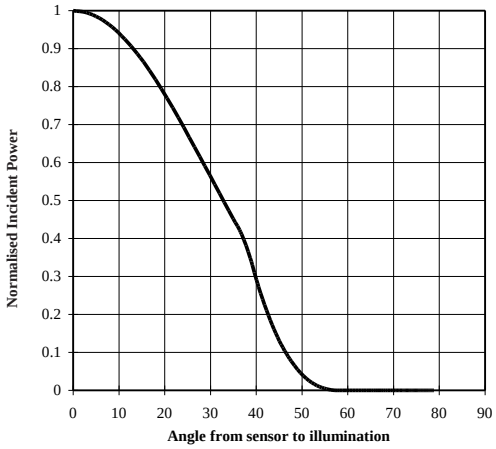
CHARACTERISTICS (T_{amb}=25°C unless otherwise stated)

Characteristic	Test Conditions.	Min.	Typ.	Max.	Units
Responsively	λ at 900nm	0.45	0.55		A/W
Active Area			5.19		mm^2
Dark Current	E = 0 Dark 1V Reverse		2	4	nA
	E = 0 Dark 10V Reverse		16	22	
Breakdown Voltage	E = 0 Dark 10µA Reverse	60	80		V
Capacitance	E = 0 Dark 0V Reverse		55		pF
	E = 0 Dark 20V Reverse		10		
Rise Time	30V Reverse 50Ω		9		ns
NEP	900nm		$19x10^{-14}$	0.45	W/√Hz

Directional characteristics



Directional Characteristics



Spectral Response